



P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
	105mΩ @ V _{GS} = -10V	-7.3A
-60V	130mΩ @ V _{GS} = -4.5V	-6.5A

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Backlighting
- Power Management Functions
- DC-DC Converters

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

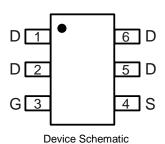
Mechanical Data

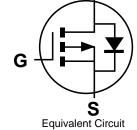
- Case: TSOT26
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 63
- Weight: 0.008 grams (Approximate)

TSOT26







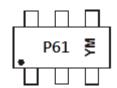


Ordering Information (Note 5)

Part Number	Case	Packaging
DMP6110SVTQ-7	TSOT26	3,000/Tape & Reel
DMP6110SVTQ-13	TSOT26	10,000/Tape & Reel

- Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 - 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 - 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 - 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.
 - 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



P61 = Product Type Marking Code YM or $\overline{Y}M$ = Date Code Marking Y = Year (ex: F = 2018) M = Month (ex: 9 = September)

Date Code Key

Year	2016	2017	2018	2019	2020	2021	2022	2023	2024
Code	D	E	F	G	Н	I	J	K	L
		•				•			

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage		V_{DSS}	-60	V
Gate-Source Voltage		V_{GSS}	±20	V
Continuous Drain Current (Note 7) V _{GS} = -10V	$T_C = +25$ °C $T_C = +70$ °C	Ι _D	-7.3 -5.8	А
Maximum Body Diode Forward Current (Note 7)	Is	-1.8	Α	
Pulsed Drain Current (380µs Pulse, 1% Duty Cycle)	I _{DM}	-24	Α	
Pulsed Source Current (380µs Pulse, 1% Duty Cycle)	I _{SM}	-24	Α	
Avalanche Current (Note 7) L = 0.1mH	I _{AS}	-19	Α	
Repetitive Avalanche Energy (Note 7) L = 0.1mH		E _{AS}	18	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 6)	$T_A = +25^{\circ}C$	Ь	1.2	W
Total Fower Dissipation (Note 0)	$T_A = +70^{\circ}C$	P _D	0.75	VV
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	В	105	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	t<10s	$R_{\theta JA}$	60	°C/W
Total Power Dissipation (Note 7)	$T_A = +25$ °C	P _D	1.8	W
Total Fower Dissipation (Note 1)	$T_A = +70^{\circ}C$	FD	1.1	VV
Thermal Resistance, Junction to Ambient (Note 7)	Steady State	$R_{\theta,JA}$	69	°C/W
Thermal Resistance, Junction to Ambient (Note 1)	t<10s	Көја	39	°C/W
Thermal Resistance, Junction to Case (Note 7)	R ₀ JC	15	°C/W	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)				•		
Drain-Source Breakdown Voltage	BV _{DSS}	-60	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current	I _{DSS}	_	_	-1	μΑ	$V_{DS} = -48V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}	_	_	-100	nA	$V_{GS} = \pm 16V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	-1		-3	٧	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$
Static Drain-Source On-Resistance		_		105	mΩ	$V_{GS} = -10V, I_D = -4.5A$
Static Diani-Source On-Resistance	R _{DS(ON)}	_	_	130	11122	$V_{GS} = -4.5V, I_D = -3.5A$
Diode Forward Voltage	V_{SD}	_	-0.7	-1.2	V	$V_{GS} = 0V, I_{S} = -1A$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	CISS	_	969	_		
Output Capacitance	Coss	_	57	_	pF	$V_{DS} = -30V, V_{GS} = 0V, f = 1.0MHz$
Reverse Transfer Capacitance	C _{RSS}	_	44	_		
Gate Resistance	R_{G}	_	13.7	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$
Total Gate Charge (V _{GS} = -4.5V)	Q_{G}	_	8.2	_		
Total Gate Charge (V _{GS} = -10V)	Q_{G}	_	17.2	_	nC	V 20V I 42A
Gate-Source Charge	Q_GS	_	3.0	_	IIC	$V_{DS} = -30V, I_{D} = -12A$
Gate-Drain Charge	Q _{GD}	_	3.1	_		
Turn-On Delay Time	t _{D(ON)}	_	4.4	_		
Turn-On Rise Time	t _R	_	23	_		$V_{GS} = -10V$, $V_{DS} = -30V$, $R_{GEN} = 3\Omega$,
Turn-Off Delay Time	t _{D(OFF)}	_	34	_	ns	I _D = -12A
Turn-Off Fall Time	t _F	_	42	_		
Body Diode Reverse Recovery Time	t _{RR}	_	13.2	_	ns	104 11/1: 1004/
Body Diode Reverse Recovery Charge	Q_{RR}	_	6.18	_	nC	$I_S = -12A$, $dI/dt = 100A/\mu s$

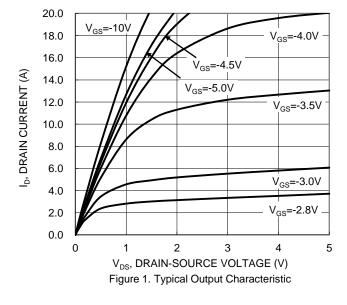
Notes: 6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

^{7.} Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate.

^{8.} Short duration pulse test used to minimize self-heating effect.

^{9.} Guaranteed by design. Not subject to product testing.





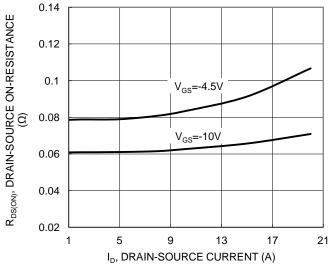


Figure 3. Typical On-Resistance vs. Drain Current and

Gate Voltage

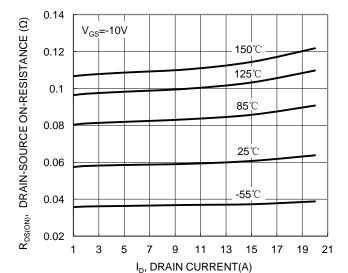
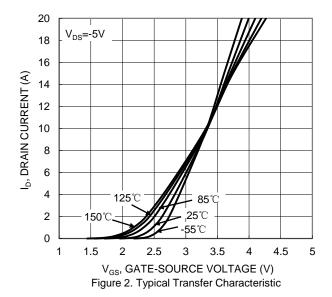
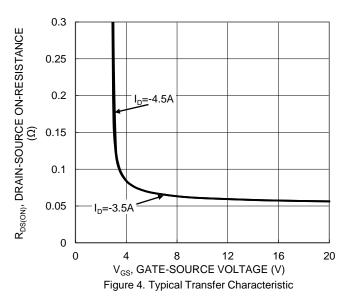


Figure 5. Typical On-Resistance vs. Drain Current and Temperature





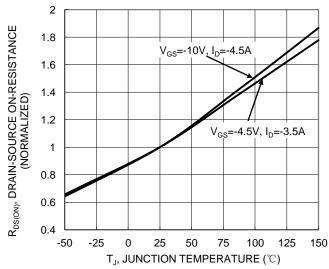


Figure 6. On-Resistance Variation with Temperature



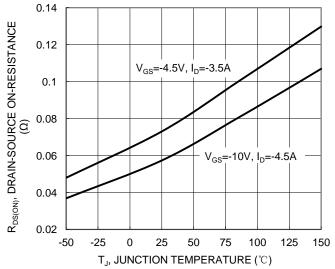
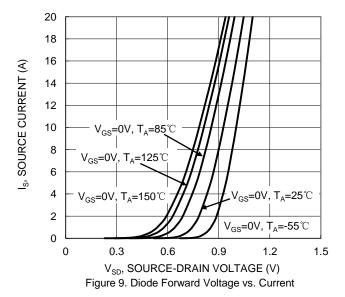


Figure 7. On-Resistance Variation with Temperature

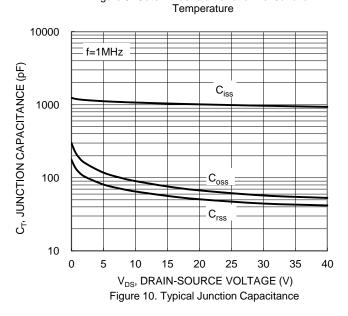


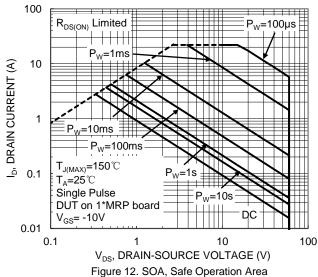
8 6 $V_{GS}(V)$ $V_{DS} = -30V, I_{D} = -12A$ 4 2 0 0 2 4 8 10 12 14 16 18

 Q_g (nC)

Figure 11. Gate Charge

2.2 $V_{\text{GS(TH)}},$ GATE THRESHOLD VOLTAGE (V) 2 1.8 $I_D = -1mA$ 1.6 $I_{D} = -250 \mu A$ 1.4 1.2 1 0.8 -50 -25 25 50 75 100 125 150 T₁, JUNCTION TEMPERATURE (°C) Figure 8. Gate Threshold Variation vs. Junction





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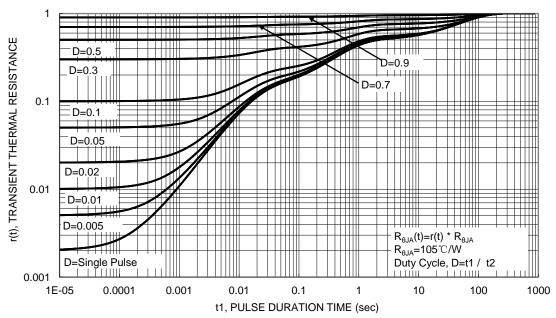


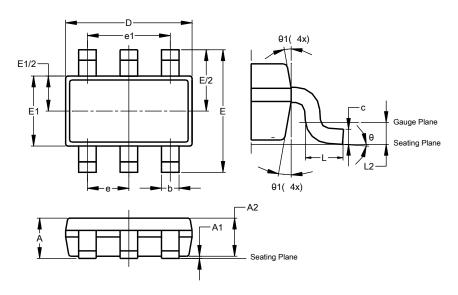
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

TSOT26

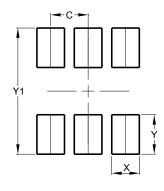


	TSOT26							
Dim	Min	Max	Тур					
Α	-	1.00	-					
A1	0.010	0.100	-					
A2	0.840	0.900	_					
۵	2.800	3.000	2.900					
Е	2.800 BSC							
E1	1.500	1.700	1.600					
b	0.300	0.450	_					
С	0.120	0.200	-					
е	0.950 BSC							
e1	1	.900 BS	С					
L	0.30	0.50	-					
L2	0	.250 BS	С					
θ	0°	8°	4°					
θ1	4°	12°	_					
Δ	All Dimensions in mm							

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

TSOT26



Dimensions	Value (in mm)
С	0.950
Х	0.700
Y	1.000
V1	3 100



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